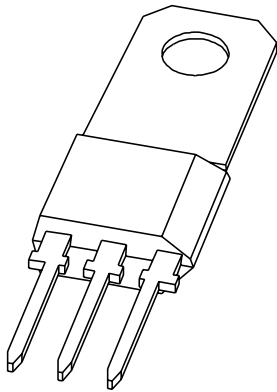


DATA SHEET



BD826; BD828; BD830 PNP power transistors

Product specification
Supersedes data of September 1994
File under Discrete Semiconductors, SC04

1997 Jun 23

PNP power transistors

BD826; BD828; BD830

FEATURES

- High current (max. 1 A)
- Low voltage (max. 80 V).

APPLICATIONS

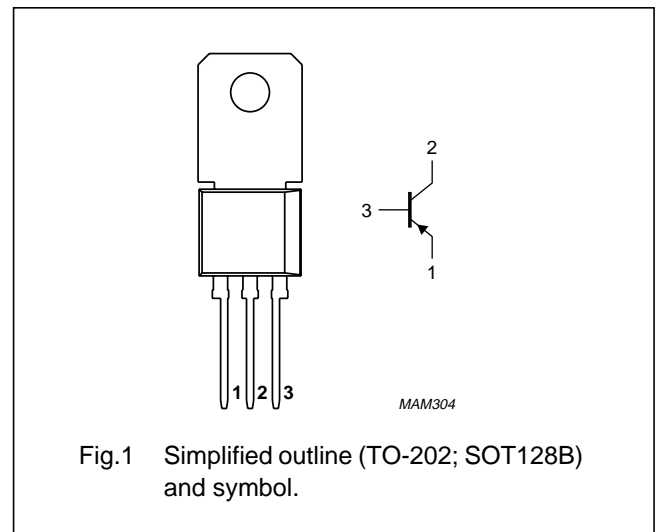
- General purpose
- Driver stages in hi-fi amplifiers and television circuits.

DESCRIPTION

PNP power transistor in a TO-202; SOT128B plastic package. NPN complements: BD825 and BD829.

PINNING

PIN	DESCRIPTION
1	emitter
2	collector, connected to metal part of mounting surface
3	base



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter				
	BD826		–	–	–45	V
	BD828		–	–	–60	V
V _{CEO}	collector-emitter voltage	open base				
	BD826		–	–	–45	V
	BD828		–	–	–60	V
	BD830		–	–	–80	V
I _{CM}	peak collector current		–	–	–1.5	A
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	–	–	2	W
		T _{mb} ≤ 50 °C	–	–	8	W
h _{FE}	DC current gain	I _C = –150 mA; V _{CE} = –2 V	40	–	250	
f _T	transition frequency	I _C = –50 mA; V _{CE} = –5 V; f = 100 MHz	–	75	–	MHz

PNP power transistors

BD826; BD828; BD830

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	BD826		–	–45	V
	BD828		–	–60	V
	BD830		–	–100	V
V _{CEO}	collector-emitter voltage	open base			
	BD826		–	–45	V
	BD828		–	–60	V
	BD830		–	–80	V
V _{EBO}	emitter-base voltage	open collector	–	–5	V
I _C	collector current (DC)		–	–1	A
I _{CM}	peak collector current		–	–1.5	A
I _{BM}	peak base current		–	–500	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	–	2	W
		T _{mb} ≤ 50 °C	–	8	W
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	in free air	62.5	K/W
R _{th j-mb}	thermal resistance from junction to mounting base		12.5	K/W

PNP power transistors

BD826; BD828; BD830

CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT	
I _{CBO}	collector cut-off current	I _E = 0; V _{CB} = -30 V	-	-	-100	nA	
		I _E = 0; V _{CB} = -30 V; T _j = 125 °C	-	-	-10	μA	
I _{EBO}	emitter cut-off current	I _C = 0; V _{EB} = -5 V	-	-	-100	nA	
h _{FE}	DC current gain	V _{CE} = -2 V; see Fig.2					
		I _C = -5 mA	40	-	-		
		I _C = -150 mA	40	-	250		
h _{FE}	DC current gain	I _C = -150 mA; V _{CE} = -2 V; see Fig.2					
			BD826-10; BD828-10; BD830-10	63	-	160	
			BD826-16; BD828-16; BD830-16	100	-	250	
V _{CEsat}	collector-emitter saturation voltage	I _C = -500 mA; I _B = -50 mA	-	-	-500	mV	
V _{BE}	base-emitter voltage	I _C = -500 mA; V _{CE} = -2 V	-	-	-1	V	
f _T	transition frequency	I _C = -50 mA; V _{CE} = -5 V; f = 100 MHz	-	75	-	MHz	

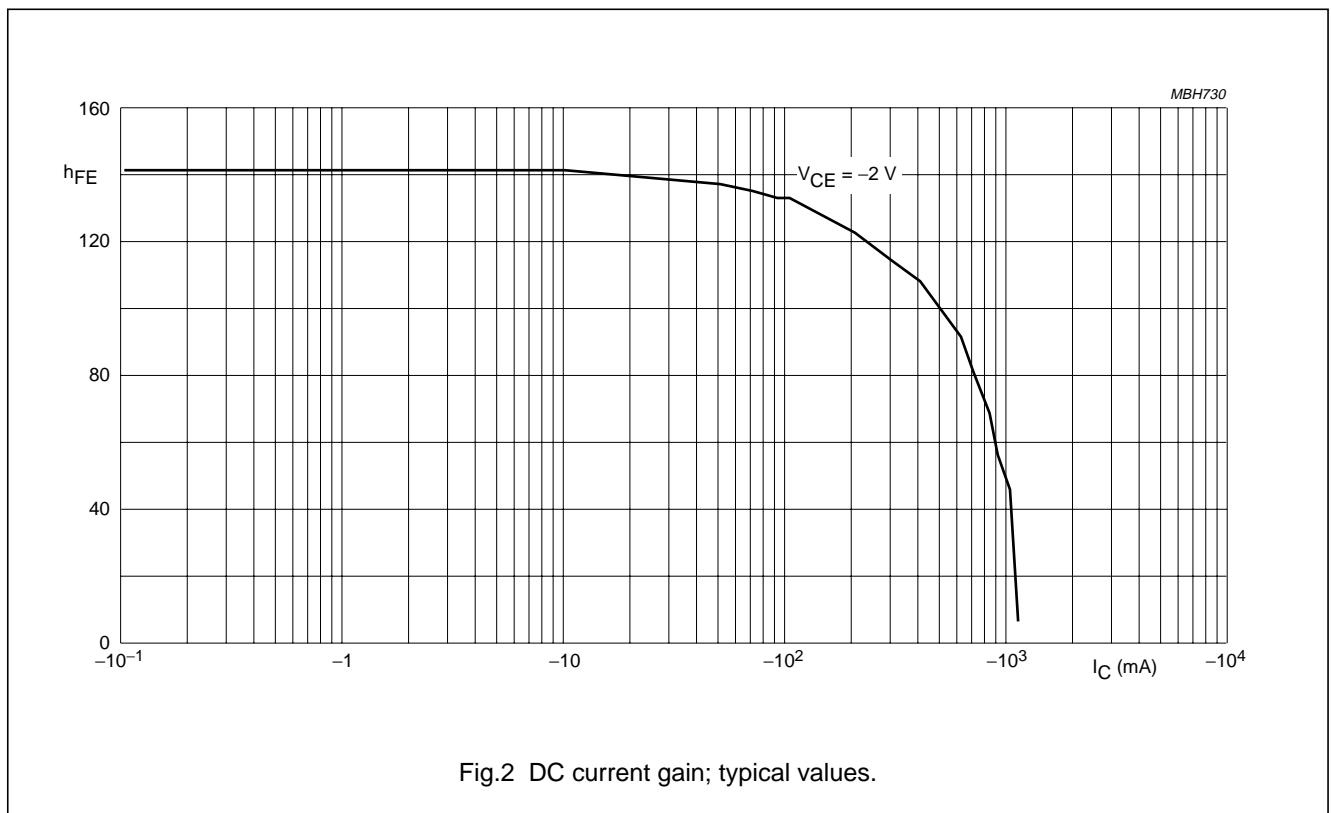


Fig.2 DC current gain; typical values.

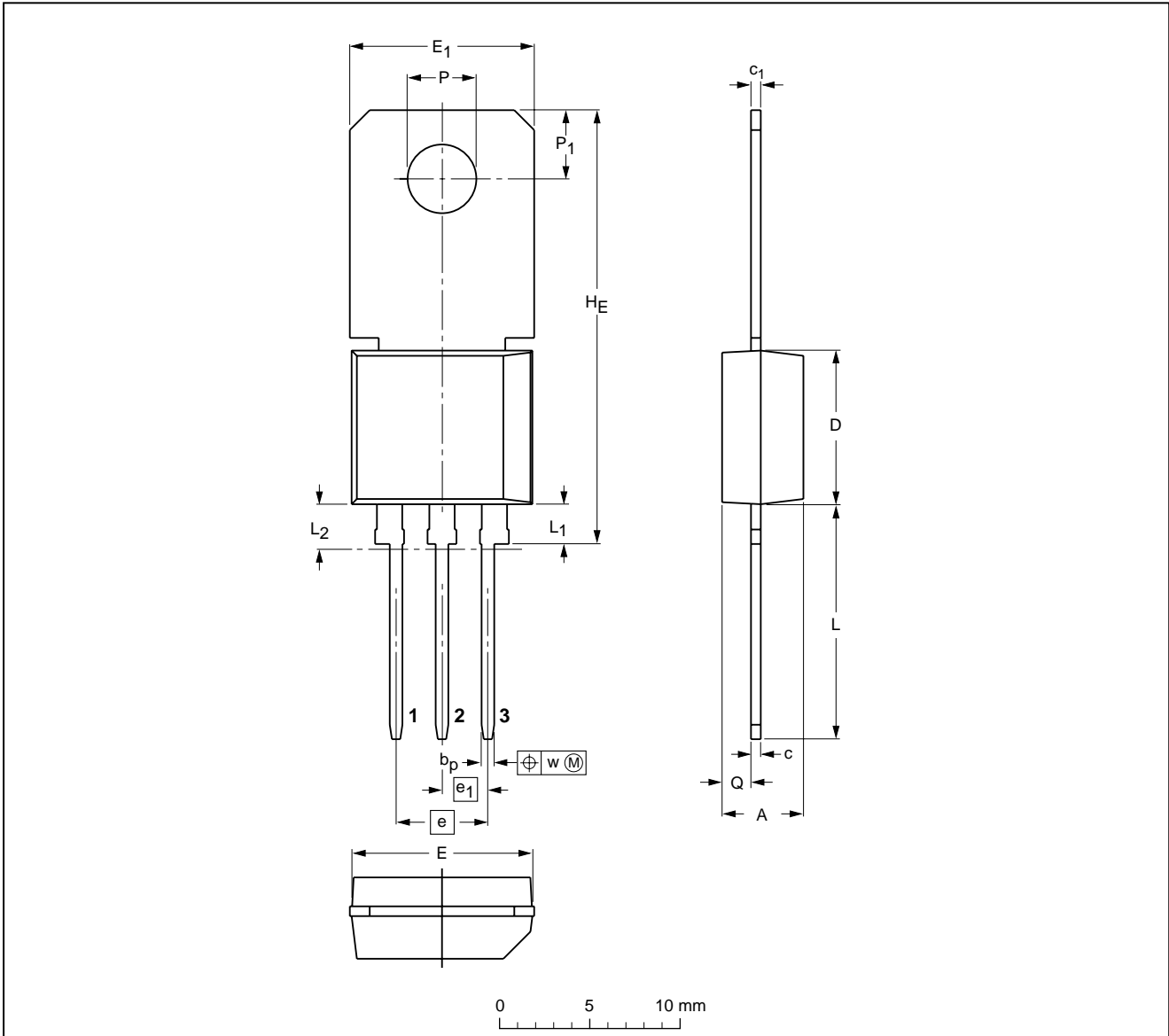
PNP power transistors

BD826; BD828; BD830

PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; with cooling fin, mountable to heatsink, 1 mounting hole; 3 leads (in-line)

SOT128B



DIMENSIONS (mm are the original dimensions)

UNIT	A	b _p	c	c ₁	D	E	E ₁	e	e ₁	H _E	L	L ₁	L ₂ ⁽¹⁾ max	P	P ₁	Q	w
mm	4.6 4.4	0.8 0.6	0.65 0.5	0.56 0.46	8.6 8.4	10.1 9.9	10.4 10.0	5.08	2.54	24.2 23.8	13.3 12.2	2.4 2.0	2.5	3.8 3.6	3.9 3.7	1.7 1.5	0.25

Note

1. Plastic flash allowed within this zone

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT128B		TO-202				97-02-28

PNP power transistors

BD826; BD828; BD830

DEFINITIONS

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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PNP power transistors

BD826; BD828; BD830

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